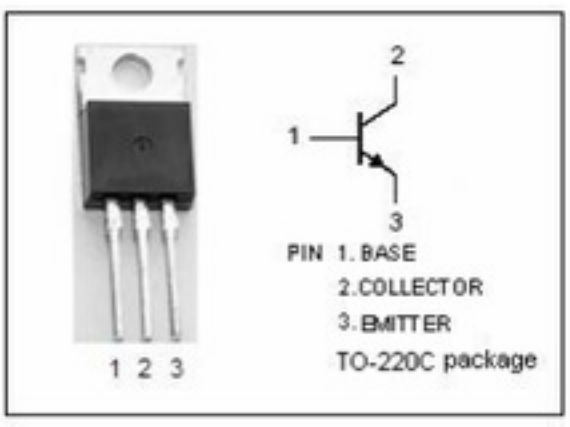
SPTECH Silicon NPN Power Transistor 2SD526

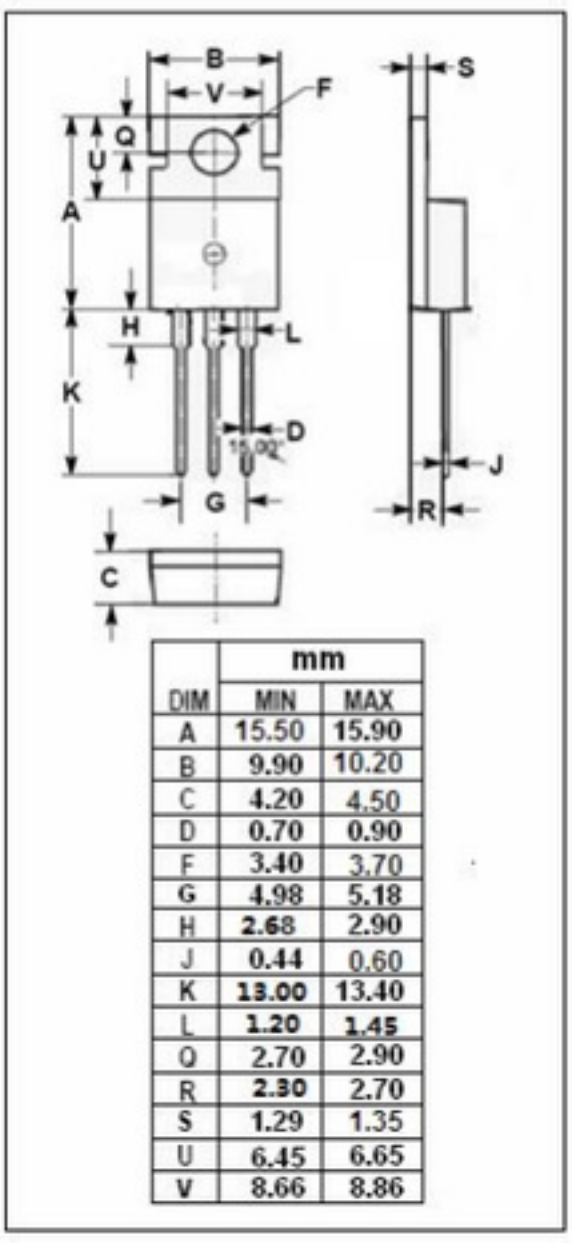


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V(Min)
- Good Linearity of h_{FE}
- Collector Power Dissipation-
  : P_C= 30W(Max)@ T_C= 25℃
- Complement to Type 2SB596

APPLICATIONS

- Designed for power amplifier applications.
- Recommended for 20~25W high fidelity audio frequency amplifier output stage applications.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	0.4	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

SPTECH Product Specification

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		0.45	1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 3A; V_{CE}= 5V		1.0	1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 80V; I_E= 0			30	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V	40		240	
h_{FE-2}	DC Current Gain	I_C= 3A; V_{CE}= 5V	15	50		
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1.0MHz		90		pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 5V	3	8		MHz

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240